

IN THE CLAIMS:

Please note that all of the claims that remain pending and under consideration, as well as those that have been added, in the above-referenced application are shown below, in clean form, for clarity. Also attached is a marked-up version to show the changes that have been made to each amended claim.

Please enter the claims as follows:

~~Ex 500
FI~~ 47. (Previously twice amended) A conductive trace at least partially formed on at least one semiconductor device component, comprising a plurality of superimposed, contiguous, mutually adhered layers, each of said layers comprising conductive polymer.

48. (Previously twice amended) The conductive trace of claim 47, wherein said conductive polymer comprises a thermoplastic conductive elastomer.

~~Ex~~ 50. (Previously amended) The conductive trace of claim 47, configured to be carried by a single semiconductor device component.

51. (Previously amended) The conductive trace of claim 47, configured to at least partially electrically connect two semiconductor device components.

52. (Previously amended three times) A semiconductor device comprising:
a semiconductor device component; and
at least one conductive trace carried by said semiconductor device component, said at least one conductive trace including a plurality of superimposed, contiguous, mutually adhered layers, each of said layers comprising conductive polymer.

53. (Previously amended) The semiconductor device of claim 52, wherein said at least one conductive trace is substantially entirely carried by said semiconductor device component.

54. The semiconductor device of claim 53, wherein said semiconductor device component comprises a layer of a carrier substrate.

55. The semiconductor device of claim 53, wherein said semiconductor device component comprises a dielectric layer disposed on an active surface of a semiconductor die.

56. (Previously amended) The semiconductor device of claim 52, wherein said conductive polymer comprises a thermoplastic conductive elastomer.

58. (Previously amended) The semiconductor device of claim 52, wherein said at least one conductive trace communicates with a contact of said semiconductor device component.

59. The semiconductor device of claim 58, wherein said semiconductor device component comprises a carrier substrate.

60. The semiconductor device of claim 58, wherein said semiconductor device component comprises a semiconductor die.

61. The semiconductor device of claim 58, wherein said semiconductor device component comprises a packaged semiconductor device.

62. The semiconductor device of claim 52, wherein said semiconductor device component comprises leads.

63. (Amended) The semiconductor device of claim 62, wherein said at least one conductive trace contacts one of said leads.

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64. (Twice amended) A semiconductor device assembly, comprising:
a carrier; and
at least one semiconductor die adjacent said carrier, said semiconductor die including bond pads;
and
conductive elements electrically connecting contacts of said carrier to corresponding bond pads,
each of said conductive elements including a plurality of superimposed, contiguous,
mutually adhered layers, each of said layers comprising the same conductive material.

65. The semiconductor device assembly of claim 64, wherein said carrier comprises a carrier substrate.

66. The semiconductor device assembly of claim 64, wherein said carrier comprises leads.

67. The semiconductor device assembly of claim 64, wherein said conductive material comprises a thermoplastic conductive elastomer.

68. The semiconductor device assembly of claim 64, wherein said conductive material comprises a metal.

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69. (Amended) A semiconductor device assembly, comprising:
a first semiconductor device component including at least one contact pad;

a second semiconductor device component including at least one contact pad; and
at least one conductive element connecting said at least one contact pad of said first
semiconductor device component to said at least one contact pad of said second
semiconductor device component, said at least one conductive element comprising a
plurality of superimposed, contiguous, mutually adhered layers comprising the same
conductive material.

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76. The semiconductor device assembly of claim 75, wherein said conductive material
comprises a conductive elastomer.

77. The semiconductor device assembly of claim 75, wherein said conductive material
comprises a metal.

78. (Amended) The semiconductor device assembly of claim 75, wherein at least one
of said first semiconductor device component and said second semiconductor device component
comprises a semiconductor die.

79. (Amended) The semiconductor device assembly of claim 78, wherein at least one
of said first semiconductor device component and said second semiconductor device component
comprises a packaged semiconductor die.

80. The semiconductor device assembly of claim 75, wherein each of said first
semiconductor device component and said second semiconductor device component comprises
at least one semiconductor die.

81. (Amended) The semiconductor device assembly of claim 75, wherein at least one of said first semiconductor device component and said second semiconductor device component comprises a carrier substrate.

82. The semiconductor device assembly of claim 81, wherein said carrier substrate includes a support structure and at least one conductive element in communication with said at least one contact pad thereof.

83. The semiconductor device assembly of claim 82, wherein at least one of said at least one conductive element and said support structure comprises a plurality of superimposed, contiguous, mutually adhered layers of material.

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84. The semiconductor device assembly of claim 75, wherein said at least one conductive element is located on a surface of each of said first and second semiconductor device components.

85. The semiconductor device assembly of claim 84, wherein said at least one conductive element extends across a peripheral edge of at least one of said first and second semiconductor device components.

86. The semiconductor device assembly of claim 80, further comprising a carrier substrate upon which at least one of said semiconductor dice is disposed.

87. The semiconductor device assembly of claim 86, further comprising at least one other conductive element connecting at least one other contact pad of at least one of said semiconductor die to at least one contact pad of said carrier substrate.

88. The semiconductor device assembly of claim 87, wherein said at least one other conductive element comprises a plurality of superimposed, contiguous, mutually adhered layers of conductive material.

89. The semiconductor device assembly of claim 88, wherein said conductive material comprises a conductive elastomer.

90. The semiconductor device assembly of claim 88, wherein said conductive material comprises metal.

Please add the following new claims:

110. 91. (New) A conductive trace at least partially formed on at least one semiconductor device component, comprising a plurality of superimposed, contiguous, mutually adhered layers, each of said layers comprising the same conductive polymer material.

111. 92. (New) The conductive trace of claim 91, wherein conductive polymer material comprises a thermoplastic conductive elastomer.

112. 93. (New) The conductive trace of claim 91, configured to be carried by a single semiconductor device component.

113. 94. (New) The conductive trace of claim 91, configured to at least partially electrically connect two semiconductor device components.

114. 95. (New) A semiconductor device comprising:
a semiconductor device component; and

at least one conductive trace carried by said semiconductor device component, said at least one conductive trace including a plurality of superimposed, contiguous, mutually adhered layers, each of said layers comprising the same conductive polymer to material.

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96. (New) The semiconductor device of claim 95, wherein said at least one conductive trace is substantially entirely carried by said semiconductor device component.

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97. (New) The semiconductor device of claim 96, wherein said semiconductor device component comprises a layer of a carrier substrate.

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98. (New) The semiconductor device of claim 96, wherein said semiconductor device component comprises a dielectric layer disposed on an active surface of a semiconductor die.

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99. (New) The semiconductor device of claim 95, wherein said conductive polymer material comprises a thermoplastic conductive elastomer.

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100. (New) The semiconductor device of claim 95, wherein said at least one conductive trace communicates with a contact of said semiconductor device component.

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101. (New) The semiconductor device of claim 100, wherein said semiconductor device component comprises a carrier substrate.

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102. (New) The semiconductor device of claim 100, wherein said semiconductor device component comprises a semiconductor die.

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103. (New) The semiconductor device of claim 100, wherein said semiconductor device component comprises a packaged semiconductor device.

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104. (New) The semiconductor device of claim 95, wherein said semiconductor device component comprises leads.

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105. (New) The semiconductor device of claim 104, wherein said at least one conductive trace contacts one of said leads.--
